

SHEET 1 OF 1

FORM PTO - 1449  SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT					ATTORNEY DOCKET NO.: ASC-049C1  APPLICANT(S): Fitzgerald SERIAL NO.: 10/774,890 FILING DATE: February 9, 2004 GROUP: 2818				
U.S. PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
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								OFFICE OF PETITIONS	
FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
MF	C102	C. Rosenblad, et al., "Strain relaxation of graded SiGe buffers grown at very high rates," <u>Materials Science and Engineering</u> , B71 (2000), pp. 20-23.							
MF	C103	E.A. Fitzgerald, et al., "Dislocations in Relaxed SiGe/Si Heterostructures," <u>Phys. Stat. Sol.</u> , (a) 171 (1999) pp. 227-238							
EXAMINER	<i>McAlliston</i>				DATE CONSIDERED				07/01/05
VER 9/00									

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<i>MS</i>	A191	2003/0080361 A1	05/01/2003	Murthy et al.			
<i>MS</i>	A192	5,821,577	10/13/1998	Crabbé et al.			
<i>MS</i>	A193	6,350,311 B1	02/26/2002	Chin et al.			
OTHER ART, JOURNAL ARTICLES, ETC.							
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)						
<i>MS</i>	C123	Examination Report for European Patent Application No. 98 931 529.6-2203, dated January 10, 2002, 4 pages.					
<i>MS</i>	C124	Examination Report for European Patent Application No. 98 931 529.6-2203, dated May 9, 2003, 5 pages.					
<i>MS</i>	C125	Examination Report for European Patent Application No. 01 973 651.1-1528, dated March 22, 2004, 3 pages.					
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<i>MS</i>	C127	Examination Report for European Patent Application No. 01 973 651.1-1528, dated November 12, 2004, 9 pages.					
<i>MS</i>	C128	Examination Report for European Patent Application No. 02 709 406.9-2203, dated May 11, 2004, 3 pages.					
<i>MS</i>	C129	Examination Report for European Patent Application No. 02 709 406.9-2203, dated March 24, 2005, 5 pages.					
<i>MS</i>	C130	International Search Report for Patent Application No. PCT/US 98/13076, dated October 27, 1998, 2 pages.					
<i>MS</i>	C131	Notice of Preliminary Rejection for Korean Patent Application No. 10-1999-7012279, dated February 21, 2002, 2 pages (English translation attached).					
<i>MS</i>	C132	Notice of Final Rejection for Korean Patent Application No. 10-1999-7012279, dated February 25, 2003 2 pages (English translation attached).					
<i>MS</i>	C133	Klauk et al., "Thermal stability of undoped strained Si channel SiGe heterostructures," Applied Physics Letter, No. 68, April 1, 1996, pgs. 1975-1977.					
<i>MS</i>	C134	Rim et al., "Enhanced Hole Mobilities in Surface-channel Strained-Si- <i>p</i> -MOSFETs," IEEE (1995), pg. 20.3.1-20.3.4.					
EXAMINER		<i>Malheon</i>		DATE CONSIDERED		<i>7/21/05</i>	